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**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

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Complete if Known

Application Number

~~Unknown~~ 10/789-038

Filing Date

~~Even Date Herewith~~ 02-27-04

First Named Inventor

Forbes, Leonard

Group Art Unit

~~Unknown~~ 2827

Examiner Name

Pham, Ly

Sheet 1 of 5

Attorney Docket No: 1303.024US2

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Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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 US Patent & Trademark Office, U.S. DEPARTMENT OF COMMERCE

<b>Complete if Known</b>	
Application Number	<del>Unknown</del> 10/789,038
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First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown 2827
Examiner Name	Pham, Ly

Sheet 2 of 5

Attorney Docket No: 1303.024US2

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	Application Number	Unknown 10/789,038
	Filing Date	Even Date Herewith 02-27-04
	First Named Inventor	Forbes, Leonard
	Group Art Unit	Unknown 2827
	Examiner Name	Pham, Ly
Sheet 3 of 5	Attorney Docket No: 1303.024US2	

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T*
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Complete if Known

Application Number	Unknown- 10/789,038
Filing Date	Even Date Herewith 02-27-04
First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown- 2827
Examiner Name	Pham, Ly

Sheet 4 of 5

Attorney Docket No: 1303.024US2

**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

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Substitute Disclosure Statement Form (PTO-1448)

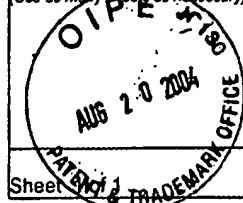
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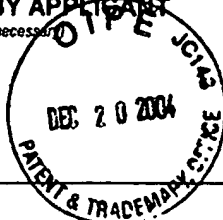
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Application Number	10/789,038
Filing Date	February 27, 2004
First Named Inventor	Forbes, Leonard
Group Art Unit	2811-2827
Examiner Name	Pham, Ly

Sheet 1 of 1

Attorney Docket No: 1303.024US2

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Examiner Initials *	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	T <sup>2</sup>
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*Pham Ly*

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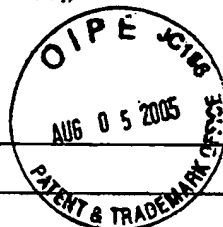


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Application Number	10/789,038
Filing Date	February 27, 2004
First Named Inventor	Forbes, Leonard
Group Art Unit	2827
Examiner Name	Pham, Ly

Attorney Docket No: 1303.024US2

**US PATENT DOCUMENTS**

Examiner Initial*	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Filing Date If Appropriate
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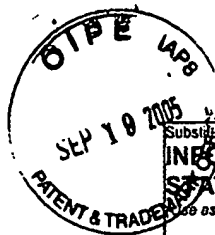
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Examiner Name	Pham, Ly

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Attorney Docket No: 1303.024US2

**US PATENT DOCUMENTS**

Examiner Initial*	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Filing Date If Appropriate
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